



R-C Thermal Model Parameters

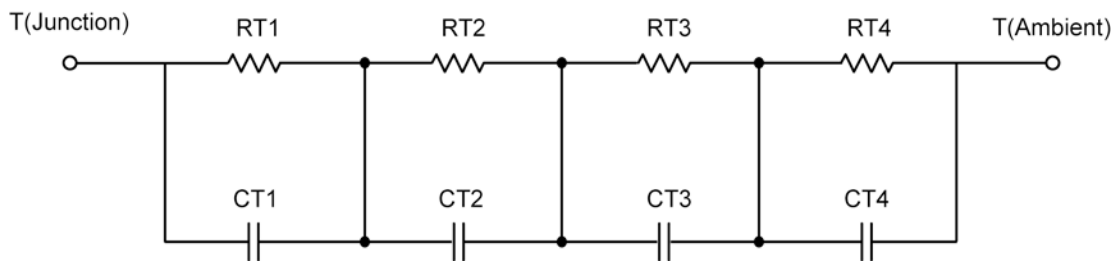
DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:
For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION

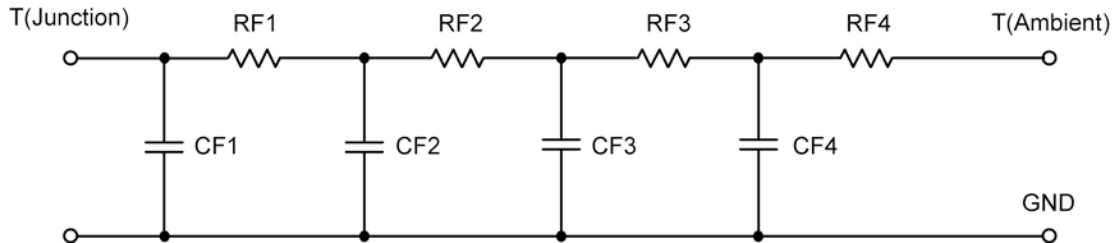


| R-C VALUES FOR TANK CONFIGURATION | | | |
|-----------------------------------|------------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RT1 | 31.5841 | 69.0737 m | N/A |
| RT2 | 736.5000 m | 132.9812 m | N/A |
| RT3 | 2.9311 | 149.4828 m | N/A |
| RT4 | 4.7483 | 148.4623 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CT1 | 2.8728 | 11.4355 m | N/A |
| CT2 | 200.9925 m | 512.4947 m | N/A |
| CT3 | 730.7719 m | 68.1290 m | N/A |
| CT4 | 26.2971 | 239.9071 m | N/A |

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.



R-C THERMAL MODEL FOR FILTER CONFIGURATION



| R-C VALUES FOR FILTER CONFIGURATION | | | |
|--|------------|------------|------|
| Thermal Resistance (°C/W) | | | |
| Junction to | Ambient | Case | Foot |
| RF1 | 643.7000 m | 108.9512 m | N/A |
| RF2 | 3.9845 | 15.2516 m | N/A |
| RF3 | 16.3586 | 254.3985 m | N/A |
| RF4 | 19.0132 | 121.3987 m | N/A |
| Thermal Capacitance (Joules/°C) | | | |
| Junction to | Ambient | Case | Foot |
| CF1 | 36.1175 m | 10.3809 m | N/A |
| CF2 | 468.1577 m | 22.6075 m | N/A |
| CF3 | 1.9545 | 25.6998 m | N/A |
| CF4 | 628.5618 m | 435.3431 m | N/A |

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

